IN THE CLAIMS

Please amend the claims as follows:

Claims 1-26 (Cancelled).

Claim 27 (Previously Presented): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

a) depositing a second thin layer on the first thin layer;

b) engraving or lithography of the second thin layer, as a function of a desired correction or corrections; and

c) etching the second sub-layer through the first sub-layer.

Claim 28 (Previously Presented): A correction method as claimed in claim 27, the desired correction including an addition of one or more patterns.

Claim 29 (Previously Presented): A correction method as claimed in Claim 27, in which one or more patterns are missing from the design, the engraving or lithography including reproduction in the second thin layer of the missing patterns.

Claim 30 (Previously Presented): A correction method as claimed in Claim 27, further comprising d) etching the first sub-layer through the second thin layer after the engraving or lithography b) and prior to the etching c).

Claim 31 (Previously Presented): A correction method as claimed in claim 30, further comprising removing the second thin layer after the etching d) of the first sub-layer through the second thin layer and prior to the etching c).

Claim 32 (Previously Presented): A correction method as claimed in Claim 27, the correction including removing one or more patterns.

Claim 33 (Previously Presented): A correction method as claimed in Claim 32, in which the one or more patterns are in excess, the engraving or lithography in the second thin layer leaving one or more blocks filling the patterns in excess.

Claim 34 (Previously Presented): A correction method as claimed in Claim 27, the correction including adding one or more missing patterns, then eliminating one or more other patterns in excess.

Claim 35 (Currently Amended): A correction method as claimed in Claim 34, further comprising, after the engraving or lithography b) and prior to the ~~engraving~~ etching c):

etching the first sub-layer through the second thin layer;

removing the second thin layer;

depositing a third thin layer on the first sub-layer; and

second lithography in the third thin layer leaving blocks filling the patterns in excess.

Claim 36 (Previously Presented): A correction method as claimed in Claim 35, the third thin layer being a dielectric layer.

Claim 37 (Previously Presented): A correction method as claimed in Claim 36, the third thin layer being a resin or polymer layer.

Claim 38 (Previously Presented): A correction method as claimed in Claim 35, the third thin layer being a positive or negative photosensitive resin layer.

Claim 39 (Previously Presented): A correction method as claimed in Claim 35, further comprising removing the third thin layer after the etching c).

Claim 40 (Previously Presented): A correction method as claimed in Claim 27, further comprising removing the first sub-layer after the etching c) of the second sub-layer through the first sub-layer.

Claim 41 (Previously Presented): A correction method as claimed in Claim 27, in which the first sub-layer is based on a first conductive, or semiconductive, or insulating material, and the second sub-layer located between the substrate and the first sub-layer is based on a second conductive, or semiconductive, or insulating material different from the first material.

Claim 42 (Previously Presented): A correction method as claimed in Claim 27, in which the first sub-layer is a sacrificial layer.

Claims 43-45 (Cancelled)

Claim 46 (Previously Presented): A method as claimed in Claim 27, the second thin layer being a dielectric layer.

Claim 47 (Previously Presented): A method as claimed in Claim 27, the second thin layer being a resin or polymer layer.

Claim 48 (Previously Presented): A method as claimed in Claim 27, the engraving or lithography being carried out by direct writing.

Claim 49 (Previously Presented): A method as claimed in Claim 27, the engraving or lithography being carried out by one or more optical particle beams.

Claim 50 (Previously Presented): A method as claimed in Claim 49, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 51 (Previously Presented): A method as claimed in Claim 49, the beam being controlled by a digital device associated with a data medium including data relative to the erroneous design and to a desired corrected design.

Claim 52 (Previously Presented): A lithography device carrying out one or more of the lithography of the method as claimed in Claim 27, comprising:

first means for producing at least one lithography beam;

second means for processing data relative to an erroneous design formed in a thin layer, and data relative to a desired corrected design, and for producing correction data following such processing; and

third means for controlling the first means, from correction data produced by the second means.

Claim 53 (New): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design

and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

a) depositing a second thin layer on the first thin layer;

b) engraving or lithography of the second thin layer, as a function of a desired correction or corrections, etching the first sub-layer through the second thin layer;

removing the second thin layer after the etching of the first sub-layer through the second thin layer; and

c) etching the second sub-layer through the first sub-layer.

Claim 54 (New): A method as claimed in Claim 53, the second thin layer being a resin or polymer layer.

Claim 55 (New): A method as claimed in Claim 53, the engraving or lithography being carried out by one or more optical particle beams.

Claim 56 (New): A method as claimed in Claim 55, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 57 (New): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

a) depositing a second thin layer on the first thin layer;

b) engraving or lithography of the second thin layer, as a function of a desired correction or corrections,

etching the first sub-layer through the second thin layer;

removing the second thin layer;

depositing a third thin layer on the first sub-layer; and

second lithography in the third thin layer leaving blocks filling the patterns in excess; and

c) etching the second sub-layer through the first sub-layer.

Claim 58 (New): A method as claimed in Claim 57, the engraving or lithography being carried out by one or more optical particle beams.

Claim 59 (New): A method as claimed in Claim 58, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 60 (New): A method as claimed in Claim 27, wherein said step of depositing said second thin layer on said first thin layer is performed such that said second thin layer covers at least a portion of said first sub-layer thereby covering said erroneous design.

Claim 61 (New): A method as claimed in Claim 27, wherein said erroneous design comprises a plurality of erroneous patterns, each erroneous pattern being an erroneous presence or an erroneous absence of a hole in said first sub-layer, and wherein said step of depositing said second thin layer is performed such that said second thin layer covers said plurality of erroneous patterns in said first sub-layer.